



# 3CD4

## PNP Silicon Low Frequency High Power Transistor



### Features:

1. Heavy output current.Small saturation voltage drop. Good temperature stability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for power amplify, Low-speed switch, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

### TECHNICAL DATA:

( $T_a = 25^\circ\text{C}$ )

Parameter name	Symbols	Unit	Specifications								Test Condition
			A	B	C	D	E	F	G	H	
Collector-Emitter Voltage	$V_{CEO}$	V	30	50	80	110	150	200	250	300	
Emitter-Base Voltage	$V_{EBO}$	V	4								
Max. Collector Current	$I_{CM}$	A	2								
Max. Collector Dissipation	$P_{CM}$	W	20								( $T_c:75^\circ\text{C}$ )
Junction Temperature	$T_{jm}$	$^\circ\text{C}$	175								
Storage Temperature	$T_{stg}$	$^\circ\text{C}$	-55~+175								
Collector-Emitter Leakage Current	$I_{CEO}$	mA	2								$V_{CE}=20\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5								A~E: $I_C=1\text{A}, I_B=0.2\text{A}$
											F~H: $I_C=0.5\text{A}, I_B=0.1\text{A}$
DC Current Gain	$h_{FE}$		Max.:240				Min.:15				A~E: $V_{CE}=10\text{V}, I_C=1.0\text{A}$
											F~H: $V_{CE}=10\text{V}, I_C=0.5\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	A	B	C	D	E	F	G	H	$I_C=5\text{mA}$
			30	50	80	110	150	200	250	300	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	4								$I_E=2\text{mA}$

### $h_{FE}$ Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
$h_{FE}$	15~25	25~40	40~55	55~80	80~120	120~240

### Outline and Dimensions: